

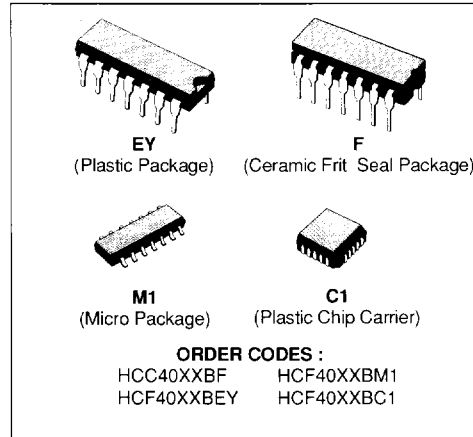
OR GATE

4071B - QUAD 2-INPUT OR GATE
4072B - QUAD 4-INPUT OR GATE
4075B - TRIPLE 3-INPUT OR GATE

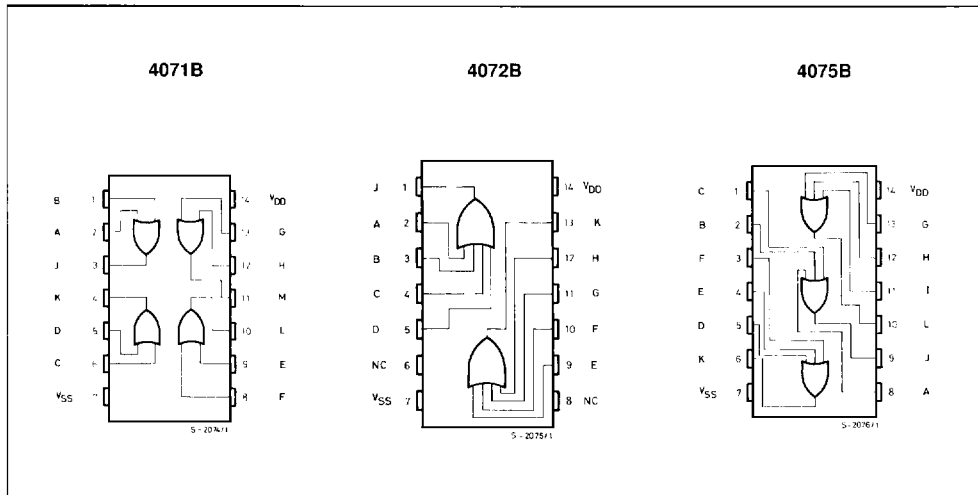
- MEDIUM-SPEED OPERATION t_{PLH} , t_{PHL} = 60ns. (typ.) AT $V_{DD} = 10V$
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N^o. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

DESCRIPTION

The **HCC4071B/4072B** and **4075B** (extended temperature range) and **HCF4071B/4072B** and **4075B** (intermediate temperature range) are monolithic integrated circuits, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.



The **HCC/HCF4071B, 4072B** and **4075B** OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of COS/MOS gates.

PIN CONNECTIONS


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD} *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
V _I	Input Voltage	- 0.5 to V _{DD} + 0.5	V
I _I	DC Input Current (any one input)	± 10	mA
P _{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for Top = Full Package-temperature Range	200 100	mW mW
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C
T _{stg}	Storage Temperature	- 65 to + 150	°C

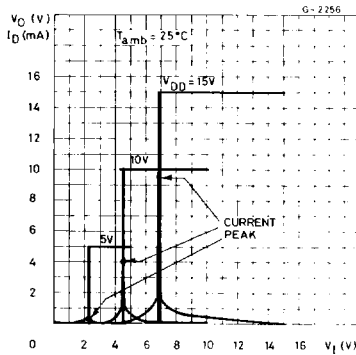
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

* All voltage values are referred to V_{SS} pin voltage.

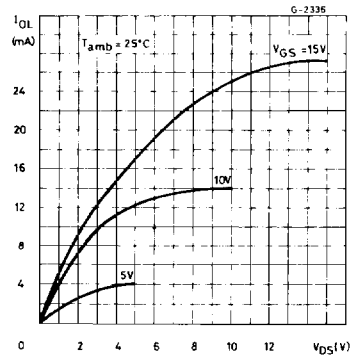
RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	V V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	°C °C

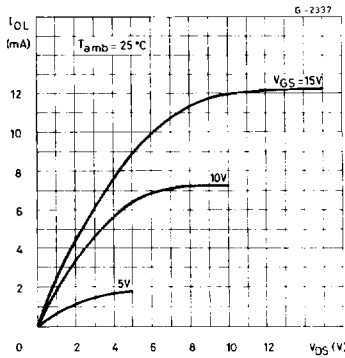
Typical Voltage and Current Transfer Characteristics.



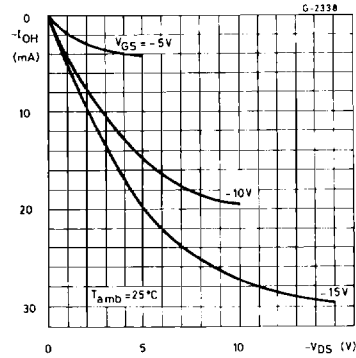
Typical Output Low (sink) Current Characteristics.



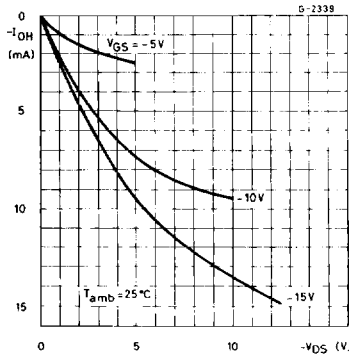
Minimum Output Low (sink) Current Characteristics.



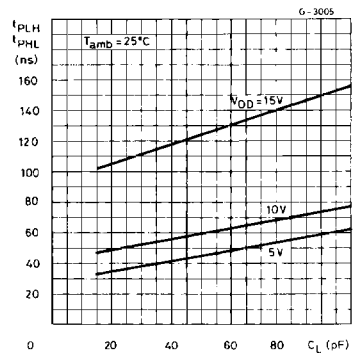
Typical Output High (source) Current Characteristics.



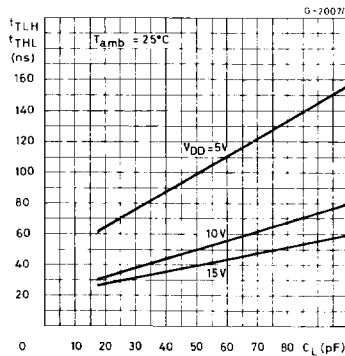
Minimum Output High (source) Current Characteristics.



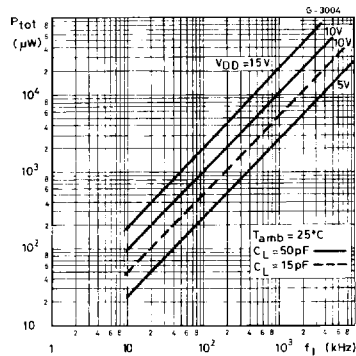
Typical Propagation Delay Time vs. Load Capacitance.



Typical Transition Time vs. Load Capacitance.

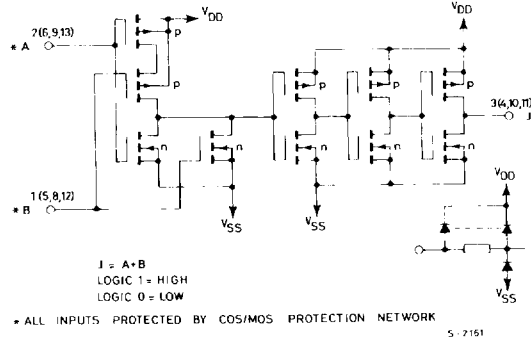


Typical Dynamic Power Dissipation vs. Frequency.

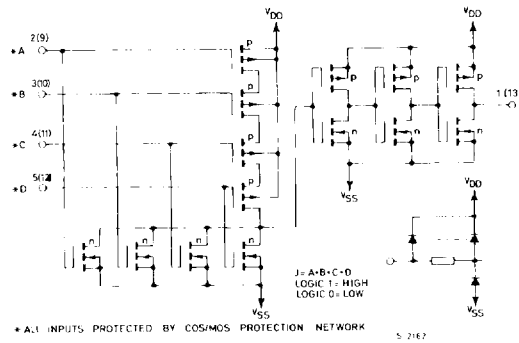


SCHEMATIC DIAGRAMS

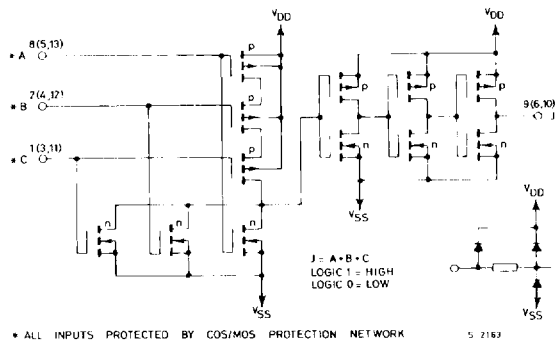
4071B – 1 of 4 identical OR gates



4072B – 1 of 2 identical OR gates



4075B – 1 of 3 identical OR gates



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit		
			V _I (V)	V _O (V)	I _O (μ A)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *			
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.	
I _L	Quiescent Current	HCC Types	0/5			5			0.25		0.01	0.25		7.5	μ A
			0/10			10			0.5		0.01	0.5		15	
			0/15			15			1		0.01	1		30	
			0/20			20			5		0.02	5		150	
		HCF Types	0/5			5			1		0.01	1		7.5	
			0/10			10			2		0.01	2		15	
			0/15			15			4		0.01	4		30	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95			V	
		0/10		< 1	10	9.95		9.95			9.95				
		0/15		< 1	15	14.95		14.95			14.95				
V _{OL}	Output Low Voltage	5/0		< 1	5			0.05			0.05		0.05	V	
		10/0		< 1	10			0.05			0.05		0.05		
		15/0		< 1	15			0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5			V	
			1/9	< 1	10	7		7			7				
			1.5/13.5	< 1	15	11		11			11				
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5			1.5			1.5		1.5	V	
			9/1	< 1	10			3			3		3		
			13.5/1.5	< 1	15			4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	-2		-1.6	-3.2		-1.15		mA	
			0/5	4.6		5	-0.64		-0.51	-1		-0.36			
			0/10	9.5		10	-1.6		-1.3	-2.6		-0.9			
			0/15	13.5		15	-4.2		-3.4	-6.8		-2.4			
		HCF Types	0/5	2.5		5	-1.53		-1.36	-3.2		-1.1			
			0/5	4.6		5	-0.52		-0.44	-1		-0.36			
			0/10	9.5		10	-1.3		-1.1	-2.6		-0.9			
0/15	13.5		15	-3.6		-3.0	-6.8		-2.4						
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36		mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9			
			0/15	1.5		15	4.2		3.4	6.8		2.4			
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36			
			0/10	0.5		10	1.3		1.1	2.6		0.9			
			0/15	1.5		15	3.6		3.0	6.8		2.4			
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input		18		± 0.1		$\pm 10^{-5}$	± 0.1		± 1	μ A	
		HCF Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1		
C _I	Input Capacitance		Any Input							5	7.5		pF		

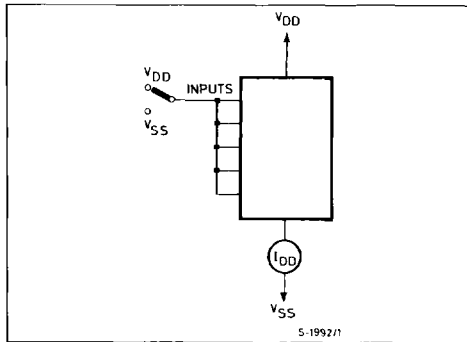
* T_{Low} = -55°C for HCC device ; -40°C for HCF device.* T_{High} = +125°C for HCC device ; +85°C for HCF device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5 V min. with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all $V_{DD} = 0.3\%/^{\circ}\text{C}$ values, all input rise and fall time = 20ns)

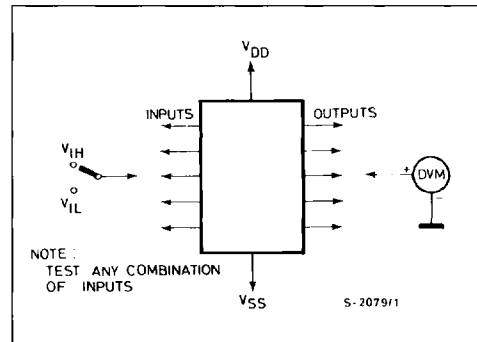
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PHL}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			15		45	90	
t_{PLH}	Propagation Delay Time		5		175	350	ns
			70		50	140	
			15		50	140	
t_{THL}, t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

TEST CIRCUITS

Quiescent Device Current.



Input Voltage.



Input Leakage Current.

